

# DAS-PMAS9B

## P-Type Mono Cell

### Product Feature

- ◇ High conversion efficiency , Up to 22.1%
- ◇ Light Induced Degradation  $\leq 2.5\%$
- ◇ PID resistant
- ◇ Power temperature coefficient  $\leq -0.38\%/^{\circ}\text{C}$
- ◇ Relative conversion efficiency (200W/m<sup>2</sup>)  $\geq 95\%$
- ◇ Lower CTM loss,better for the high efficiency module

### Quality Control

- ◇ The accuracy of the efficiency test is controlled at  $\pm 0.1\%$
- ◇ IV/EL/Appearance 100% automatic inspection
- ◇ Calibration Cell source to Fraunhofer ISE

### Management System Certification

- ◇ ISO 9001:2015 Quality Management System
- ◇ ISO 14001:2015 Environmental Management System
- ◇ ISO 45001:2018 Occupational Health and Safety Management System

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## Product Features

Dimension:	158.75mmx158.75mm±0.25mm
Cell Thickness:	180μm±20μm
Front side:	0.06±0.01mm wide bus bars, 110 finger grids, SiN
Back side:	1.67±0.1 mm wide discontinuous soldering pads, Aluminum back surface field

## Temperature Coefficients

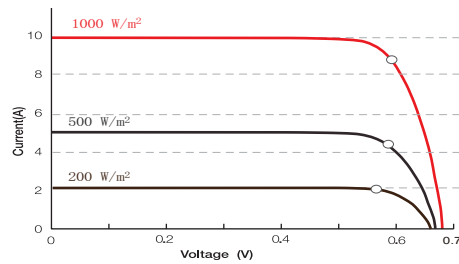
Current Temperature Coefficient	Tkcurrent: +0.048 %/K
Voltage Temperature Coefficient	Tkvoltage: -0.31 %/K
Power Temperature Coefficient	Tkpower: -0.38 %/K

## Electric Performance

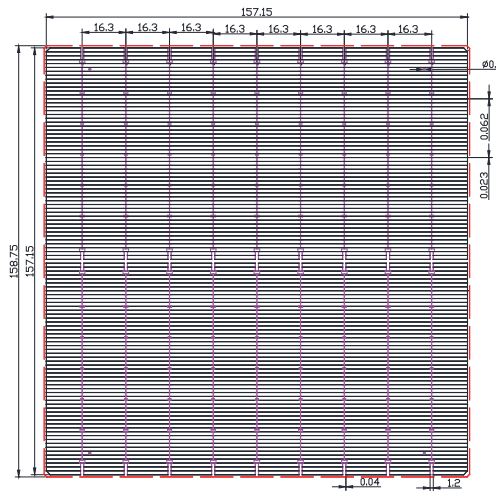
Eff(%)	Pmpp(W)	Ump(V)	Imp(A)	Uoc(V)	Isc(A)	FF(%)
22.40%	5.64	0.577	9.795	0.679	10.233	81.34
22.30%	5.62	0.576	9.777	0.678	10.222	81.26
22.20%	5.59	0.575	9.752	0.677	10.207	81.15
22.10%	5.57	0.574	9.728	0.676	10.195	81.02
22.00%	5.54	0.573	9.704	0.675	10.185	80.88
21.90%	5.52	0.572	9.681	0.674	10.168	80.80
21.80%	5.49	0.571	9.657	0.673	10.154	80.69
21.70%	5.47	0.569	9.644	0.672	10.134	80.58
21.60%	5.44	0.567	9.648	0.671	10.129	80.49
21.50%	5.42	0.565	9.639	0.670	10.107	80.42
21.40%	5.39	0.564	9.609	0.669	10.093	80.26

- Standard Test Conditions: 1000W/ m<sup>2</sup>, AM 1.5, 25°C
- Specifications and data are only for reference.

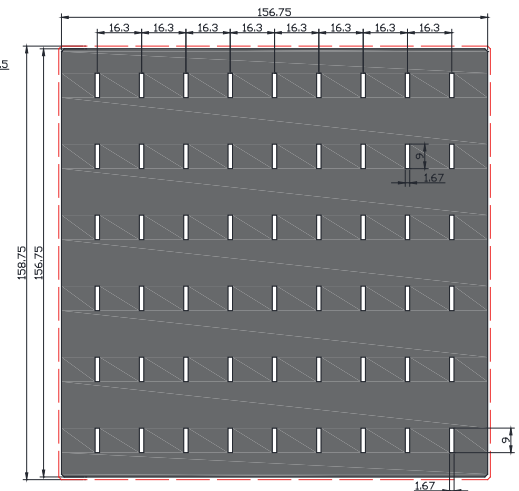
## IV Curve



## Front side



## Rear side



## Spectral Response (SR)

